Roll	No
KUII	INU

Semester: 1st

## National Institute of Technology, Hamirpur (HP)

## Name of Examination: B. Tech Mid-Term Examination (January -2021)

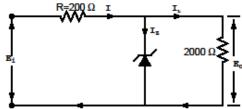
Department: Electronics & Communication Engineering

Title of the Course: **Basic Electronics Engineering**Course Code: **EC-101** 

Time: 90 Minutes Maximum Marks: 30

#### Note:

- 1. All the questions are compulsory.
- 2. The Marks of each question are indicated against the question.
- Q. 1. Explain Hall's Effect. Derive Continuity Equation for a semiconductor material. [7 Marks]
- **Q. 2.** Determine the range of input voltage for the Zener Diode circuit shown below to maintain 30 Volts across the  $2000\Omega$  Load. Assuming that series resistance R= $200\Omega$  and Zener current rating is 25mA.



[3 Marks]

- **Q. 3.** A Silicon Diode operates at a forward voltage of 0.3Volts. Calculate the factor by which the current will be multiplied, if temperature increases from  $27^{\circ} C \& 125^{\circ} C$ .
- [5 Marks]
- **Q. 4.** Discuss and draw the V-I characteristics of P-N junction diode under forward and reversed biased condition.
- [5 Marks]
- **Q. 5.** With suitable diagram, discuss the concept of space charge region in detail.
- [3 Marks]
- **Q. 6** Describe the characteristics of Ideal Diode. Also discuss differences between Ideal and Practical Diodes.
- [3 Marks]
- **Q. 7** Explain the working principle of Zener Diode and its characteristics in detail.
- [4 Marks]



# इलेक्ट्रॉनिक्स एवं संचार अभियंत्रिकी विभाग राष्ट्रीय प्रौद्योगिकी संस्थान हमीरपुर - १७७००५ (हि.प्र.) भारत

## EC-101 Basic Electronics Engineering

Section-A(Compulsory)

Jan 16,2023

Mid term Examination [Time Duration: 1.5 Hour]

Roll No.: .....

Max. Marks

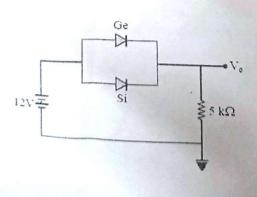
Note:Section-A is compulsory. Attempt any six questions from Section-B.

## 30 Marks

- Answer the question below in short.
  - [6 Marks]
  - (a) Is the temperature coefficient of resistance of a semiconductor is positive or negative? Explain. (b) Why the mobility of holes is smaller than the electrons in Si Semiconductors?
  - (c) An n-type semiconductor is electrically negative. Comment on it.
  - (d) Why an ordinary diode suffers avalanche breakdown rather than zener breakdown?
  - (e) For a reverse bias pn junction diode, does the transition region increase or decrease in width?
  - (f) Peak inverse voltage(PIV) of a rectifier is required to be high or low?

## Section-B(Attempt any six questions)

- 2. The intrinsic resistivity of a germanium semiconductor at 300K is 0.47 ohm-m.The electron mobility at 300K in Ge is 0.39  $m^2/V - s$ . The hole mobility at 300K in Ge is 0.19  $m^2/V - s$ . Calculate the density of electrons in the intrinsic material. Also calculate the drift velocity of holes and electrons for an electric field(E) =  $10^4 V/m$ .
- 3. Discuss the Energy Band structure of an open circuit p-n junction and analyse quantitatively the same for its current components.
- 4. In the circuit below Ge and Si Diodes are used in parallel.Si and Ge diode conducts at 0.7V and 0.3V respectively.
  - (a) Find the value of Vo in the figure below.
  - (b) In the following figure if Ge diode is reversed then how much is the change in the value of



[4 Marks]



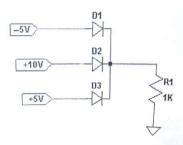
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5. The resistor in the circuit shown in figure below has a value of  $R=4k\Omega$  , the Zener diode break. down voltage is  $V_z = 5.6V$  and the power rating of the zener diode is P = 6.5mW. Determine the maximum diode current and the maximum power supply voltage that can be applied without [4 Marks] damaging the diode. 0.25cm

$$V_{PS} = 10 \text{ V} \xrightarrow{=} V_{Z} = 5.6 \text{ V}$$

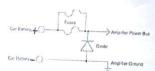
6. Assuming diode to be ideal, what is the voltage across the resistance R1 having value 1K as shown [4 Marks] in the figure?



5Ma

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7. The practical circuit of a car battery connected with the amplifier(stereo system) is shown in the figure below. What is the purpose of the diode used in the circuit. (Recall pn junction V-I [4 Marks]



8. Consider the circuit in Figure below, assuming the practical diode model. Assume  $V_{on}=0.7V$  for

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- (a) Sketch the output voltage waveform across  $R_L$ .
- (b) Sketch the output voltage waveform across  $R_L$  when diode D2 is burnt in the circuit.

